

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT2303N3T**

CHIP SIZE	0.56 * 0.43 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	64,000 pcs

Maximum Ratings(Ta=25°C)

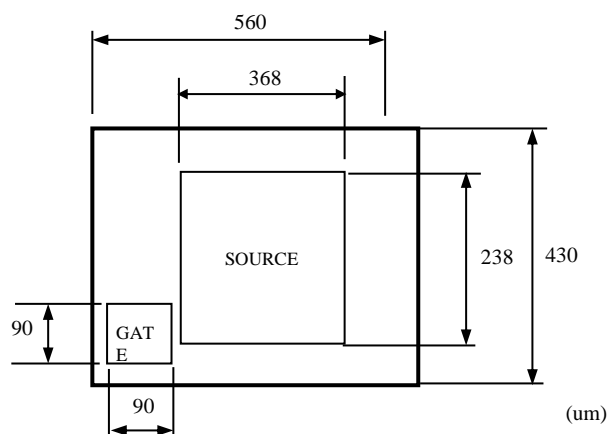
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.8	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	VGSS	±21			V	IG=±10uA
2	IGSS			±10	uA	VGS=±20.0V VDS=0V
3	IDSS			500	nA	VDS=30.0V VGS=0V
4	BVDSS	33			V	ID=250uA
5	VTH 1	1.0		2.5	V	ID=250uA
6	VTH 2	1.0		2.5	V	ID=1mA
7	Ron 1		0.15	0.24	Ω	ID=1.4A VGS=10V
8	Ron 2		0.25	0.35	Ω	ID=1.4A VGS=4.5V
9	Ron 3		0.28	0.38	Ω	ID=1.4A VGS=4.0V
10	VSD	0.5		1.1	V	IS=200mA
11	YFS	200			mS	ID=500mA VDS=10V

※ Built-in ZD between Gate and Source.



TENTATIVE

NOTE: